

# BCR8FM-12LB

600V - 8A - Triac

Medium Power Use

R07DS1186EJ0201 Rev.2.01 Feb. 19, 2019

#### **Features**

I<sub>T (RMS)</sub>: 8 A
 V<sub>DRM</sub>: 600 V
 Tj: 150 °C

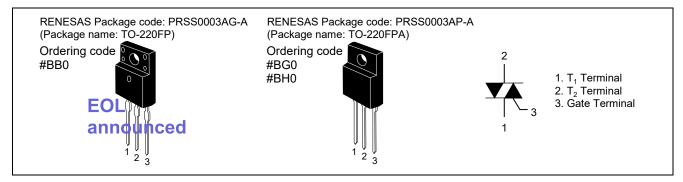
I<sub>FGTI</sub>, I<sub>RGTI</sub>, I<sub>RGT III</sub>: 30 mA(20mA) Note5

Insulated Type

• Planar Passivation Type

• Viso: 2000V

#### **Outline**



## **Application**

Motor control, Heater control, Power supply, Solid state relay, and other general purpose AC control applications.

## **Maximum Ratings**

| Parameter  | Symbol           | Voltage class | Unit |
|--|------------------|---------------|------|
|  |                  | 12            |      |
| Repetitive peak off-state voltageNote1                 | VDRM             | 600           | V    |
| Non-repetitive peak off-state voltage <sup>Note1</sup> | V <sub>DSM</sub> | 720           | V    |

| Parameter                      | Symbol               | Ratings     | Unit             | Conditions   |
|--------------------------------|----------------------|-------------|------------------|--|
| RMS on-state current           | I <sub>T (RMS)</sub> | 8           | Α                | Commercial frequency, sine full wave                 |
|                                |                      |             |                  | 360°conduction,                                      |
|                                |                      |             |                  | Tc = 114°C (#BB0, #BH0) Note2                        |
|                                |                      |             |                  | Tc = 107°C (#BG0) Note2                              |
| Surge on-state current         | ITSM                 | 80          | Α                | 50 Hz sinewave 1 full cycle, peak value,             |
|                                |                      |             |                  | non-repetitive                                       |
| I <sup>2</sup> t for fusion    | l <sup>2</sup> t     | 26          | A <sup>2</sup> s | Value corresponding to 1 cycle of half wave          |
|                                |                      |             |                  | 50 Hz, surge on-state current                        |
| Peak gate power dissipation    | $P_{GM}$             | 5           | W                |  |
| Average gate power dissipation | P <sub>G</sub> (AV)  | 0.5         | W                |  |
| Peak gate voltage              | V <sub>GM</sub>      | 10          | V                |  |
| Peak gate current              | I <sub>GM</sub>      | 2           | Α                |  |
| Junction Temperature           | Tj                   | -40 to +150 | °C               |  |
| Storage temperature            | Tstg                 | -40 to +150 | °C               |  |
| Isolation voltage Note7        | Viso                 | 2000        | V                | Ta=25°C, AC 1 minute,                                |
|                                |                      |             |                  | T <sub>1</sub> • T <sub>2</sub> • G terminal to case |

Notes: 1. Gate open.

2. Please refer to the Ordering Information.

## **Electrical Characteristics**

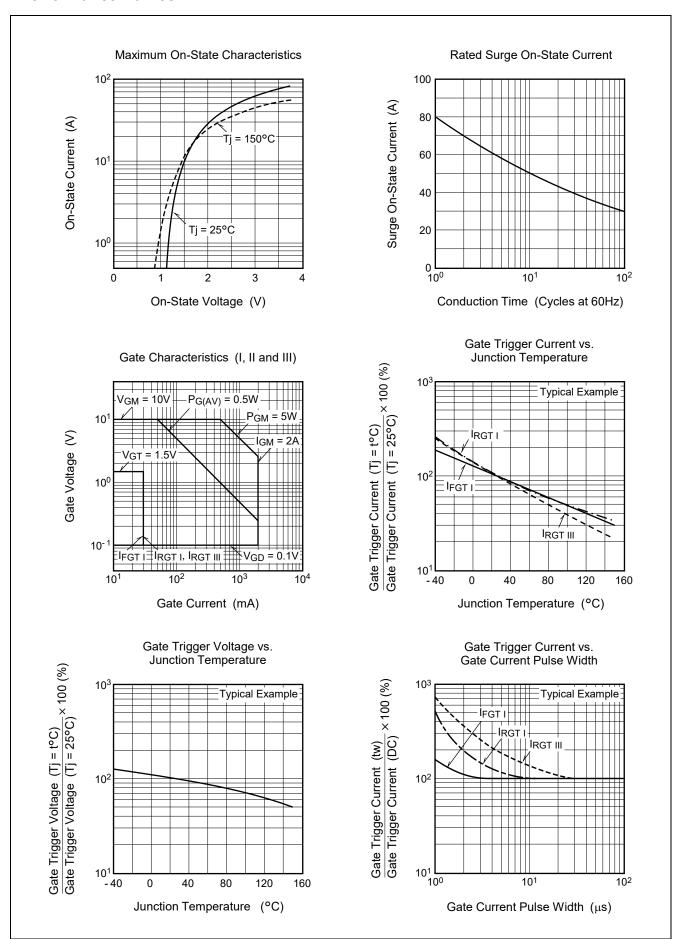
| Parameter                             |      | Symbol                | Min. | Тур. | Max.     | Unit | Test conditions  |
|---------------------------------------|------|-----------------------|------|------|----------|------|--|
| Repetitive peak off-state cur         | rent | I <sub>DRM</sub>      | _    | _    | 2.0      | mA   | Tj = 150°C, V <sub>DRM</sub> applied                               |
| On-state voltage                      |      | V <sub>TM</sub>       | _    | _    | 1.6      | V    | Tc = 25°C, I <sub>TM</sub> = 12 A,<br>instantaneous measurement    |
| Gate trigger voltage <sup>Note3</sup> | I    | V <sub>FGTI</sub>     | _    | _    | 1.5      | V    | Tj = 25°C, $V_D$ = 6 V, $R_L$ = 6 Ω,                               |
|                                       | II   | $V_{RGTI}$            | _    | _    | 1.5      | V    | $R_G = 330 \Omega$   |
|                                       | III  | V <sub>RGTIII</sub>   | _    | _    | 1.5      | V    |  |
| Gate trigger curent <sup>Note3</sup>  | I    | I <sub>FGTI</sub>     | _    | _    | 30 Note6 | mA   | Tj = 25°C, $V_D$ = 6 V, $R_L$ = 6 Ω,                               |
|                                       | II   | I <sub>RGTI</sub>     | _    | _    | 30 Note6 | mA   | $R_G = 330 \Omega$   |
|                                       | III  | I <sub>RGTIII</sub>   | _    | _    | 30 Note6 | mA   |  |
| Gate non-trigger voltage              |      | $V_{GD}$              | 0.2  | _    | _        | V    | Tj = 125°C, V <sub>D</sub> = 1/2 V <sub>DRM</sub>                  |
|                                       |      |                       | 0.1  | _    | _        |      | Tj = 150°C, V <sub>D</sub> = 1/2 V <sub>DRM</sub>                  |
| Thermal resistance                    |      | R <sub>th (j-c)</sub> | _    | _    | 3.6      | °C/W | Junction to case <sup>Note4</sup><br>(#BB0, #BH0) <sup>Note2</sup> |
|                                       |      |                       | _    | _    | 4.3      | °C/W | Junction to case <sup>Note4</sup><br>(#BG0) <sup>Note2</sup>       |
| Critical-rate of rise of off-state    |      | (dv/dt)c              | 10   | _    | _        | V/μs | Tj = 125°C   |
| commutation voltage <sup>Note5</sup>  |      |                       | 1    |      | _        |      | Tj = 150°C   |

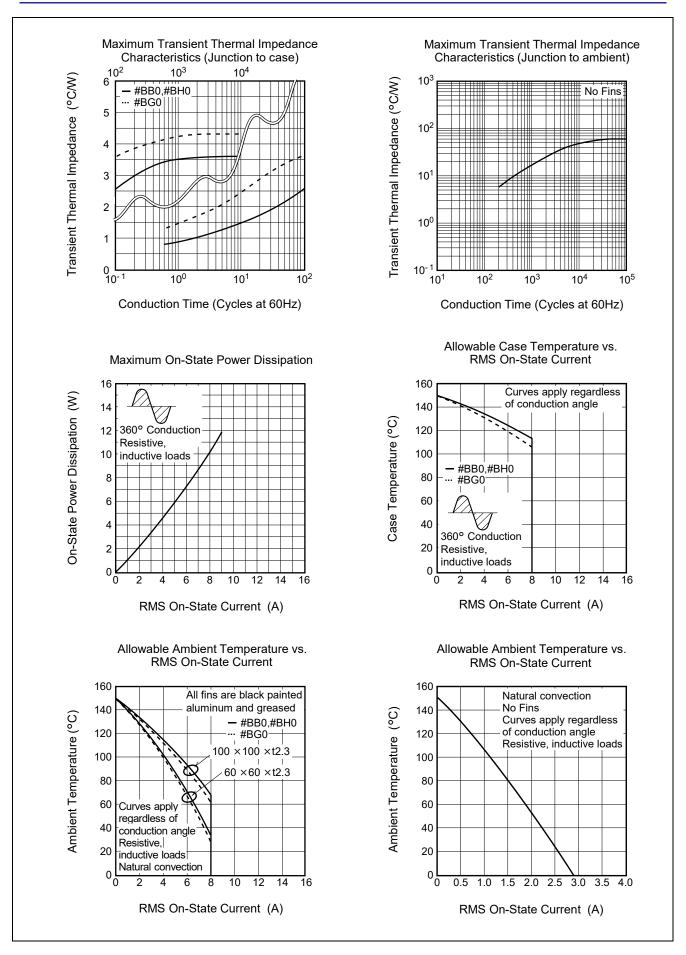
Notes: 3. Measurement using the gate trigger characteristics measurement circuit.

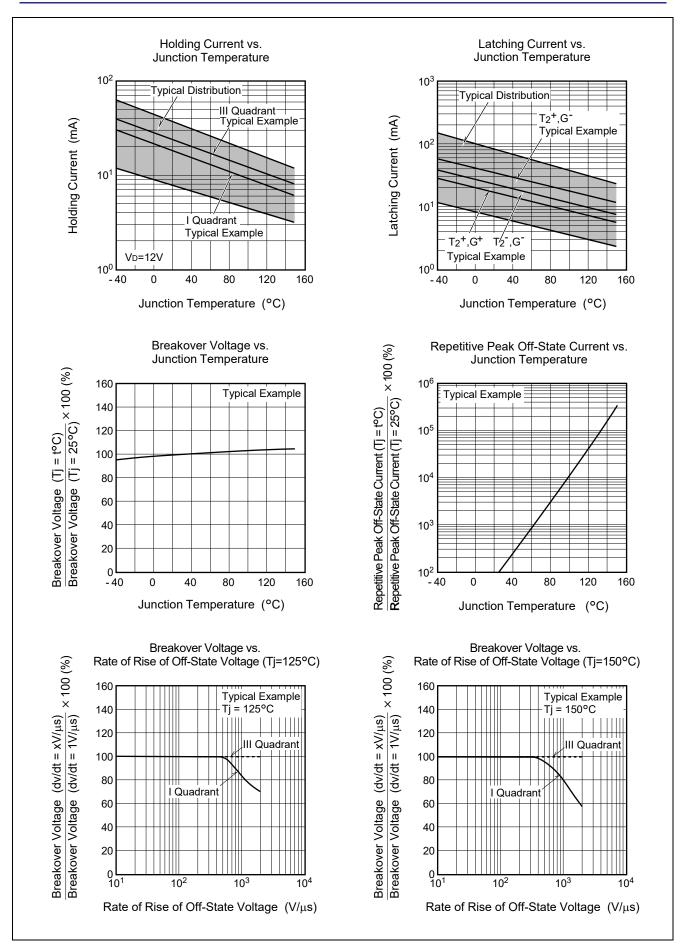
- 4. The contact thermal resistance  $R_{th(c-f)}$  in case of greasing is  $0.5^{\circ}\text{C/W}$ .
- 5. Test conditions of the critical-rate of rise of off-state commutation voltage is shown in the table below.
- 6. High sensitivity (I<sub>GT</sub> ≤ 20 mA) is also available. (I<sub>GT</sub> item:1)
- 7. Make sure that your finished product containing this device meets your safe isolation requirements. For safety, it's advisable that heatsink is electrically floating.

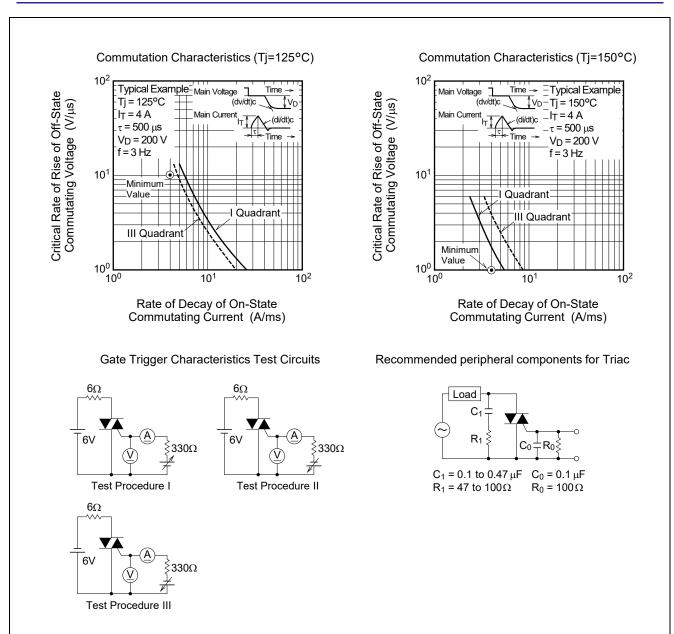
| Test conditions  | Commutating voltage and current waveforms (inductive load)                         |
|--|--|
| 1. Junction temperature  Tj = 125°C/150°C  2. Rate of decay of on-state commutating current  (di/dt)c = -4 A/ms  3. Peak off-state voltage  V <sub>D</sub> = 400 V | Supply Voltage  Main Current  Main Voltage  (di/dt)c  Time  Main Voltage  (dv/dt)c |

#### **Performance Curves**









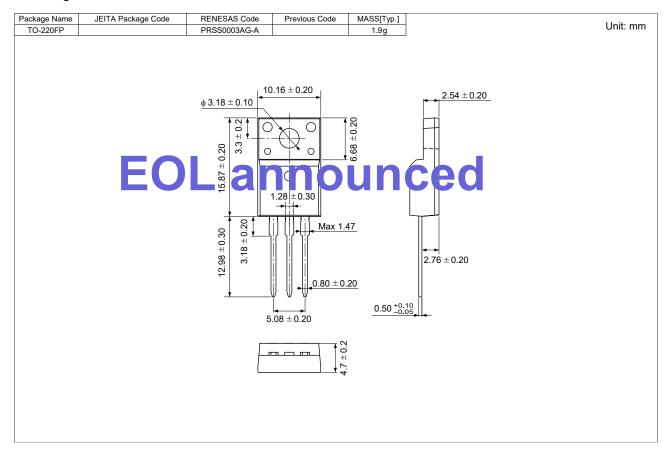
# **Package Dimensions**

Ordering code: #BG0, #BH0

| DDCCOO              | S Code | Previous Code | MASS (Typ) [g] |
|---------------------|--------|---------------|----------------|
| - PR55000           | )3AP-A | TO-220FPA     | 1.65           |
| 10.0±0.3<br>E:0∓6:9 | 2.7±0  | .2            | 1.65 Unit: mr  |

# **Package Dimensions**

# Ordering code: #BB0 <EOL announced>



# **Ordering Information**

| Orderable Part Number | Package   | Quantity Note8 | Remark                                    | Status          |
|-----------------------|-----------|----------------|---|-----------------|
| BCR8FM-12LB#BG0       | TO-220FPA | 50 pcs./ tube  | Straight type                             | Mass Production |
| BCR8FM-12LB-1#BG0     | TO-220FPA | 50 pcs./ tube  | Straight type, Igт item:1                 |                 |
| BCR8FM-12LB-□□#BG0    | TO-220FPA | 50 pcs./ tube  | □□:Lead form type                         |                 |
| BCR8FM-12LB1□□#BG0    | TO-220FPA | 50 pcs./ tube  | □□:Lead form type, I <sub>GT</sub> item:1 |                 |
| BCR8FM-12LB#BH0       | TO-220FPA | 50 pcs./ tube  | Straight type                             |                 |
| BCR8FM-12LB-1#BH0     | TO-220FPA | 50 pcs./ tube  | Straight type, Igт item:1                 |                 |
| BCR8FM-12LB-□□#BH0    | TO-220FPA | 50 pcs./ tube  | □□:Lead form type                         |                 |
| BCR8FM-12LB1□□#BH0    | TO-220FPA | 50 pcs./ tube  | □□:Lead form type, I <sub>GT</sub> item:1 |                 |
| BCR8FM-12LB#BB0       | TO-220FP  | 50 pcs./ tube  | Straight type                             | EOL announced   |
| BCR8FM-12LB□□#BB0     | TO-220FP  | 50 pcs./ tube  | □□:Lead form type                         |                 |

Notes: 8. Please confirm the specification about the shipping in detail.

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